DOCUMENT CHANGE REQUEST

DCR number 1602	Changes required for: General	Originator: Steve Thacker
Date: 2024/01/12	Date sent: 2023/10/06	Organisation: ESCC Executive Secretariat
Status: IMPLEMENTED		

Title:	TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH100N6		
Number:	5205/022	Issue:	8

Other documents affected:

Page:

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Paragraph:

2.12.2

Original wording:

Source-to-Drain Diode Forward Voltage, VSD, Drift Value limit: ±5%

Proposed wording:

Source-to-Drain Diode Forward Voltage, VSD, Drift Value limit: ±15%

See attached spec mark-up for details.

Justification:

This DCR is raised on behalf of Manufacturer STM.

STM justification:
The latest TID result showed a drift around 10% on wafers 8 inch on VSD test.
In order to accept the wafers 8 inch, the drift value +-5% should be changed to +-15% for VSD.

Attachments:
escc5205022iss_draft_9_in_review.docx
Modifications:
N/A
Approval signature:
Date signed:
2024-01-12